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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/043,736	01/09/2002	Andrew Yeoh	042390.P10048D	7389
75	90 03/05/2004		EXAMINER	
Michael A. Be	ichael A. Bernadicou Vu, Hung K			JNG K
BLAKELY, SC	KOLOFF, TAYLOR	& ZAFMAN LLP		
Seventh Floor			ART UNIT	PAPER NUMBER
12400 Wilshire	Boulevard		2811	
Los Angeles, C	CA 90025-1026			

DATE MAILED: 03/05/2004

Please find below and/or attached an Office communication concerning this application or proceeding.

			<u> </u>
	Application No.	Applicant(s)	
	10/043,736	YEOH, ANDREW	
Office Action Summary	Examiner	Art Unit	
	Hung K. Vu	2811	
The MAILING DATE of this communication Period for Reply	n appears on the cover sheet w	ith the correspondence address -	-
A SHORTENED STATUTORY PERIOD FOR R THE MAILING DATE OF THIS COMMUNICATI - Extensions of time may be available under the provisions of 37 C after SIX (6) MONTHS from the mailing date of this communicatii - If the period for reply specified above is less than thirty (30) days - If NO period for reply is specified above, the maximum statutory - Failure to reply within the set or extended period for reply will, by Any reply received by the Office later than three months after the earned patent term adjustment. See 37 CFR 1.704(b).	ON. FR 1.136(a). In no event, however, may a con. , a reply within the statutory minimum of thir period will apply and will expire SIX (6) MON statute, cause the application to become Af	reply be timely filed ty (30) days will be considered timely. ITHS from the mailing date of this communication BANDONED (35 U.S.C. § 133).	ation.
Status			
1)⊠ Responsive to communication(s) filed on 2a)⊠ This action is FINAL . 2b)□ 3)□ Since this application is in condition for al closed in accordance with the practice unit	This action is non-final.	•	s is
Disposition of Claims			
4) Claim(s) 18-29 is/are pending in the appli 4a) Of the above claim(s) 22 and 29 is/are 5) Claim(s) is/are allowed. 6) Claim(s) 18-21 and 23-28 is/are rejected. 7) Claim(s) is/are objected to. 8) Claim(s) are subject to restriction and all of the appli subject to restriction and all of the appli subject to restriction and all of the appli subject to restriction and appli subject to restriction and all of the appli subject to restriction and applied subject to restrictio	withdrawn from consideration	•	
Application Papers			
9) The specification is objected to by the Exa 10) The drawing(s) filed on is/are: a) Applicant may not request that any objection to Replacement drawing sheet(s) including the control of the c	accepted or b) objected to othe drawing(s) be held in abeyar orrection is required if the drawing	nce. See 37 CFR 1.85(a). (s) is objected to. See 37 CFR 1.12	
Priority under 35 U.S.C. § 119			
12) Acknowledgment is made of a claim for fo a) All b) Some * c) None of: 1. Certified copies of the priority docu 2. Certified copies of the priority docu 3. Copies of the certified copies of the application from the International B * See the attached detailed Office action for	ments have been received. ments have been received in A priority documents have been ureau (PCT Rule 17.2(a)).	pplication No received in this National Stage	
Attachment(s) 1) ☑ Notice of References Cited (PTO-892) 2) ☑ Notice of Draftsperson's Patent Drawing Review (PTO-94 3) ☑ Information Disclosure Statement(s) (PTO-1449 or PTO/S	8) Paper No(Summary (PTO-413) s)/Mail Date nformal Patent Application (PTO-152)	
Paper No(s)/Mail Date <u>08/11/03</u> .	6) Other:		

DETAILED ACTION

Election/Restrictions

1. Applicant's election of Invention of Embodiment 2 of Figure 3B in Paper No. 12/03/03 is acknowledged. Because applicant did not distinctly and specifically point out the supposed errors in the restriction requirement, the election has been treated as an election without traverse (MPEP § 818.03(a)).

Applicant's election without traverse of Invention of Embodiment 2 of Figure 3B in Paper No. 12/03/03 is acknowledged.

Claims 22 and 29 are withdrawn from further consideration pursuant to 37 CFR 1.142(b) as being drawn to a nonelected Invention, there being no allowable generic or linking claim.

Election was made without traverse in Paper No. 12/03/03.

Claim Rejections - 35 USC § 102

2. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

Claims 18-21 and 23-28 are rejected under 35 U.S.C. 102(e) as being anticipated by Pavate et al. (PN 6,32,819).

With regard to claim 18, Pavate et al. discloses, as shown in Figure 2, a semiconductor device comprising:

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a silicon substrate (110) [Col. 5, lines 44-52];

a patterned dielectric layer (204) on the substrate;

a metal layer (210) on the dielectric layer, the metal layer comprising a first metal and a second metal, wherein the second metal is present in an amount sufficient to increase the hardness of the metal layer [Col. 6, lines 8-16 and 56-65. Note that it is inherent that the metal layer doped with alloy elements will cause precipitation or a phase change in the metal layer].

With regard to claim 19, Pavate et al. discloses the second metal is a solute that improves the hardness of the metal layer [Col. 6, lines 56-65].

With regard to claim 20, Pavate et al. discloses the second metal is beryllium [Col. 3, lines 66-67 and Col. 6, line 14].

With regard to claim 21, Pavate et al. discloses the first metal is copper [Col. 3, lines 64-65 and Col. 6, lines 8-13].

With regard to claim 23, it is inherent that the first metal (copper) has a crystalline lattice and being doped with the second metal (beryllium), atoms of the second metal occupy interstitial sites in the crystal lattice [Col. 3, lines 63-67 and Col. 6, lines 8-16].

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With regard to claims 24 and 28, it is inherent that the metal layer is doped with the second metal (beryllium) will cause precipitations so that the second metal is present in the metal layer as large grained precipitate islands [Col. 3, lines 63-67 and Col. 6, lines 8-16].

With regard to claims 25 and 27, Pavate et al. discloses the doped material is uniformly mixing in a molten copper material, therefore, it is inherent that the second metal is a finely dispersed solute rich phase[Col. 3, lines 63-67, Col. 4, lines 1-9, and Col. 6, lines 8-16].

With regard to claim 26, Pavate et al. discloses, as shown in Figure 2, a semiconductor device comprising:

a silicon substrate (110) [Col. 5, lines 44-52];

a patterned dielectric layer (204) on the substrate;

a metal layer (210) comprising copper and beryllium [Col. 3, lines 63-67 and Col. 6, lines 8-16].

3. Claims 18-21 and 26 are rejected under 35 U.S.C. 102(e) as being anticipated by Edelstein et al. (PN 6,181,012).

With regard to claim 18, Edelstein et al. discloses, as shown in Figure 2, a semiconductor device comprising:

a silicon substrate (52) [Col. 6, lines 53-55];

a patterned dielectric layer (no label or 100) on the substrate;

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a metal layer (76 or 78) on the dielectric layer, the metal layer comprising a first metal and a second metal [Col. 4, lines 29-40 and Col. 6, lines 29-33. Note that it is inherent that the metal layer doped with alloy elements will cause precipitation or a phase change in the metal layer and to increase the hardness of the metal layer].

With regard to claim 19, it is inherent that the second metal is a solute that improves the hardness of the metal layer [Col. 4, lines 29-40 and Col. 6, lines 29-33].

With regard to claim 20, Edelstein et al. discloses the second metal is beryllium [Col. 4, lines 29-40 and Col. 6, lines 29-33].

With regard to claim 21, Edelstein et al. discloses the first metal is copper [Col. 4, lines 29-40 and Col. 6, lines 29-33].

With regard to claim 26, Edelstein et al. discloses, as shown in Figure 2, a semiconductor device comprising:

- a silicon substrate (52) [Col. 6, lines 53-55];
- a patterned dielectric layer (no label or 100) on the substrate;
- a metal layer (76 or 78) comprising copper and beryllium [Col. 4, lines 29-40 and Col. 6, lines 29-33].

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Response to Arguments

4. Applicant's arguments with respect to claims 18 and 26 have been considered but are moot in view of the new ground(s) of rejection.

Conclusion

5. Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Hung K. Vu whose telephone number is (571) 272-1666. The examiner can normally be reached on Mon-Thurs 6:00-3:30, alternate Friday 7:00-3:30, Eastern Time.

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If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Eddie C. Lee can be reached on (571) 272-1732. The Central Fax Number for the organization where this application or proceeding is assigned is (703) 872-9306.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

Vu

February 19, 2004

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